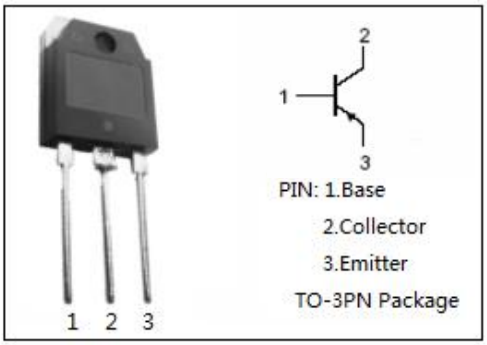
isc Silicon PNP Power Transistor 2SA1943N

DESCRIPTION

- High Current Capability
- High Power Dissipation
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -230V(Min)
- Complement to Type 2SC5200N
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

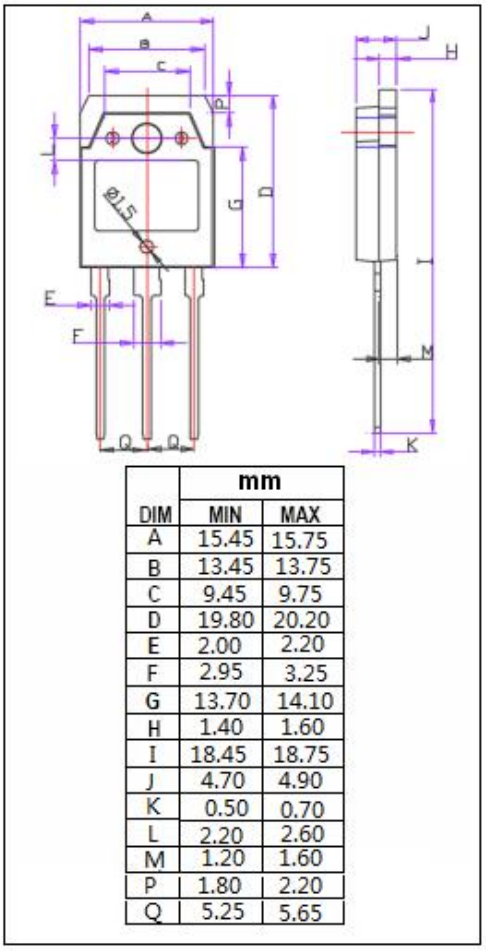


APPLICATIONS

- Power amplifier applications
- Recommend for 100W high fidelity audio frequency amplifier output stage applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-230	V
V_{CEO}	Collector-Emitter Voltage	-230	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current-Continuous	-1.5	A
P_C	Collector Power Dissipation @ T_C=25℃	150	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	15.45	15.75
B	13.45	13.75
C	9.45	9.75
D	19.80	20.20
E	2.00	2.20
F	2.95	3.25
G	13.70	14.10
H	1.40	1.60
I	18.45	18.75
J	4.70	4.90
K	0.50	0.70
L	2.20	2.60
M	1.20	1.60
P	1.80	2.20
Q	5.25	5.65

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA ; I_B= 0	-230			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -8.0A; I_B=- 0.8A			-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -7A ; V_{CE}=-5V			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -230V ; I_E= 0			-5	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-5	μA
h_{FE-1}	DC Current Gain	I_C= -1A ; V_{CE}= -5V	80		160	
h_{FE-2}	DC Current Gain	I_C= -7A ; V_{CE}= -5V	35			